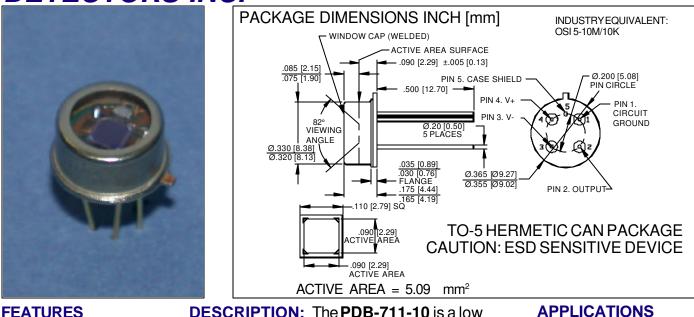
PHOTONIC DETECTORS INC.

Detector Amplifier Hybrid, Blue Enhanced Type PDB-711-10

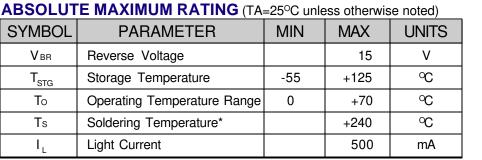


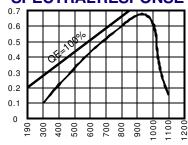
- 10 Khz bandwidth
- Internal10 MOhm gain
- Low offset voltage •
- Low input bias current

noise, medium speed, blue enhanced silicon photodiode integrated with a low noise JFET monolithic transimpedance op-amp. There is an internal 10 MOhm feedback gain resistor which limits the bandwidth to 10KHz.

- Medical diagnostic
- Low signal applications
- Color analysis
- Analytical chemistry

SPECTRALRESPONSE





WAVELENGTH(nm)

RESPONSIVITY (A/W)

*1/16 inch from case for 3 secs max

PHOTODIODE ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| SYMBOL | CHARACTERISTIC | TESTCONDITIONS | MIN | TYP | MAX | UNITS |
|--------|----------------------------|--------------------------------|-----|-----------------------|------|--------------------|
| lsc | Short Circuit Current | H = 100 fc, 2850 K | 45 | 65 | | μA |
| ΙD | Dark Current | H = 0, V _R = 10 V | | 1.0 | 5.0 | nA |
| Rsh | Shunt Resistance | $H = 0, V_{R} = 10 \text{ mV}$ | .5 | 2 | | GΩ |
| TC Rsh | RSH Temp. Coefficient | $H = 0, V_{R} = 10 \text{ mV}$ | | -8 | | % / °C |
| CJ | Junction Capacitance | $H = 0, V_{R} = 10 V^{**}$ | | 15 | | pF |
| λrange | Spectral Application Range | Spot Scan | 350 | | 1100 | nm |
| λρ | Spectral Response - Peak | Spot Scan | | 950 | | nm |
| VBR | Breakdown Voltage | I = 10 µµA | 100 | 125 | | V |
| NEP | Noise Equivalent Power | VR = 10 V @ Peak | | 2.5x10 ⁻¹⁴ | | W/ V Hz |
| tr | Response Time | $RL = 1 K\Omega V_R = 10 V$ | | 15 | | nS |

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications PAGE 1 OF 2 are subject to change without notice. ** f = 1 MHz [FORM NO. 100-PDB-711-10 REV A]

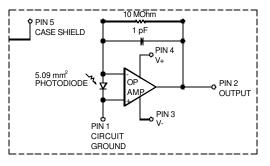
PHOTONIC DETECTORS INC.

AMPLIFIER SPECIFICATION TA=25° C and VS=± 15 vdc UNLESS OTHERWISE NOTED

| CHARACTERISTIC | TEST CONDITIONS | MIN | ТҮР | MAX | UNITS | |
|--|---|------|--------------------------|-----|------------------|--|
| FEEDBACKNETWORK10 MEG Ω RESISTER,1pF* CAPACITOR | THINFILMRESISTOR TRIMMED TO±5% *TOL ±5% | | 10 | | MEG Ω | |
| | INITIALOFFSET | | 0.75 | 2.0 | mV | |
| INPUT OFFSET VOLTAGE | LONG TERM OFFSET STABILITY | | 15 | | μV/MONTH | |
| INPUT BIAS CURRENT | OFFSETCURRENT, VCM=0 | | 5 | 20 | рА | |
| INPUT IMPEDANCE | DIFFERENTIAL | | 1 X 10 ⁻¹² 3 | | Ω∥pF | |
| | COMMONMODE | | 1 X 10 ⁻¹² ∥3 | | | |
| INPUT VOLTAGE RANGE | COMMONMODE | ±11 | ±12 | | V | |
| INFUT VOLTAGE HANGE | COMMONMODE REJECTION VCM±10 V | 76 | 90 | | | |
| INPUT VOLTAGE NOISE | VOLTAGE 0, 1 Hz TO 10 Hz | | 2 | | μV р-р | |
| INFUT VOLTAGENOISE | VOLTAGE 0, f=10 Khz | | 30 | | nV∕√Hz | |
| INPUT CURRENTNOISE | f=1 Khz | | 1.8 | | fA / \sqrt{Hz} | |
| FREQUENCY RESPONSE | UNITY GAIN, SMALL SIGNAL | 0.8 | 1.0 | | MHz | |
| FREQUENCE RESPONSE | SLEW RATE, UNITY GAIN | 1.0 | 1.8 | | V/µs | |
| OPEN LOOP GAIN | vo= ± 10 V, R _L =10 K Ω | 300 | 1000 | | V/mV | |
| OUTPUT CHARACTERISTICS | VOLTAGE @ $R_L=10 K\Omega$ | ±12 | ±13 | | V | |
| | VOLTAGE @ $R_1 > 5K\Omega$ | ±11 | ±12.3 | | V | |
| POWER SUPPLY | OPERATING RANGE | ±4.5 | ±15 | ±18 | V | |

AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25°C UNLESS OTHERWISE NOTED)

| PARAMETER | MIN | MAX | UNITS |
|----------------------------|------|------|-------|
| SUPPLYVOLTAGE | ±4.5 | ±18 | V |
| INTERNAL POWER DISSIPATION | | 500 | mW |
| STORAGETEMPERATURE | -55 | +150 | ° C |
| OPERATINGTEMPERATURE | 0 | +70 | ° C |



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